L Numbe	er Hits	S Search Text		
1	125		DB	Time stamp
		with sensory.cim.	USPAT; US-PGPUB;	2004/10/12 16:23
i			EPO; JPO;	
			DERWENT;	
		·	IBM TDB	
2	1023	(method with accelerometer).clm.	USPAT;	2004/10/12 16:24
			US-PGPUB;	10.24
			EPO; JPO;	
			DERWENT;	1
3	60	(mothed with a	IBM_TDB	
]	00	(method with accelerometer).clm. and MEMS	USPAT;	2004/10/12 16:27
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	. ∤
4	382	(438/50).CCLS.	IBM_TDB	
		(300) 300 100 110 1	USPAT;	2004/10/12 16:27
			US-PGPUB; EPO; JPO;	*
			DERWENT;	1
1_			IBM TDB	1
5	631	(438/48).CCLS.	USPAT;	2004/10/12 16:27
			US-PGPUB;	2004/10/12 16:2/
			EPO; JPO;	
			DERWENT;	[
6	400	(420 (50) 500 5	IBM TDB	
1 6	428	(438/52).CCLS.	USPAT;	2004/10/12 16:27
1			US-PGPUB;	
1			EPO; JPO;	
	1	·	DERWENT;	1
7	62	((438/50).CCLS.) and protect\$3.clm.	IBM_TDB	
	02	(130750).ccbs.) and protect\$3.clm.	USPAT;	2004/10/12 16:28
			US-PGPUB;	i
			EPO; JPO;	
			DERWENT;	
8	66	((Ge or Germanium) with (etch\$3 or	IBM_TDB USPAT;	2004/10/10 15 25
		attack\$3) with (KOH or (potassium adi	US-PGPUB;	2004/10/12 17:35
		hydroxide)))	EPO; JPO;]
			DERWENT;	
9			IBM TDB	
9	85	((releas\$3 with etch\$3) with (KOH or	USPAT;	2004/10/12 17:35
		(potassium adj hydroxide)))	US-PGPUB;	1 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2
			EPO; JPO;	
ļ		•	DERWENT;	1
10	62	((silicon-germanium) with protect\$3)	IBM_TDB	
		((orrigon germanium) with protect\$3)	USPAT;	2004/10/12 17:38
			US-PGPUB;	
			EPO; JPO;	
1			DERWENT; IBM TDB	
-	44	((Ge or Germanium) same (protect\$3 adj	USPAT;	2004/10/12 17:21
]	(Coating or layer or material or film)))	US-PGPUB;	2004/10/12 17:21
		and ((polysilicon or nucleat\$3) adj layer)	EPO; JPO;	
			DERWENT;	
_		(MDMC)	IBM TDB	
_	62	(MEMS or micromechanical or	USPAT;	2004/10/08 19:22
		microelectromechanical or	US-PGPUB;	13.22
	ļ	microstructure\$1) and ((pattern\$3 or	EPO; JPO;	
	1	etch\$3 or remov\$3 or form\$3) with	DERWENT;	1
_	102	(backside or back-side)).clm. (sensor\$1 or transducer\$1).clm. and	IBM_TDB	
	102	((pattern\$3 or etch\$3 or remov\$3 or	USPAT;	2004/10/08 19:21
		form\$3) with (backside or back-side)).clm.	US-PGPUB;	
			EPO; JPO;	ļ
			DERWENT;	
_	36	(Ge or Germanium) with (nucleat\$3 adj	IBM_TDB	2004/16/15
		layer)	USPAT; US-PGPUB;	2004/10/12 11:35
			EPO; JPO;	
	}		DERWENT;	
			IBM TDB	

r					
-	389	MEMS and etch\$3 and (sacrificial).clm.	USPAT; US-PGPUB;	2004/01/12 09:1	0
			EPO; JPO;		
			DERWENT;		
			IBM TDB		
-	112	((216/2).CCLS.) and (protect\$3).clm.	USPAT;	2004/10/08 19:2	3
			US-PGPUB;	2001/10/00 15.2	J
			EPO; JPO;		
1			DERWENT;		
1	1 1.0		IBM_TDB		
-	142		USPAT;	2004/10/12 11:5	4
İ		microelectromechanical or	US-PGPUB;		
		microstructure\$1) and (etch\$3 and	EPO; JPO;		
		(protective adj layer)).clm.	DERWENT;		
_	2	("6368885").PN.	IBM_TDB		
		(0300003).FN.	USPAT;	2004/10/12 11:3	5
			US-PGPUB;		
	İ		EPO; JPO;		
			DERWENT;		
-	6	("5527744" "5903380" "6080675"	IBM_TDB USPAT	2004/10/12 11:3	_
		"6140689" "6204087" "6225145").PN.	ODEMI	2004/10/12 11:3	ا د
-	0	6368885.URPN.	USPAT	2004/10/12 11:3	ا ۽
-	25	\	USPAT;	2004/10/12 11:3	2
		microelectromechanical or	US-PGPUB;	2004/10/12 11:4.	-
		microstructure\$1) and (etch\$3 and	EPO; JPO;		ĺ
		(aluminum adj layer)).clm.	DERWENT;		
İ			IBM TDB		
-	219		USPAT;	2004/10/12 11:44	ıΙ
		microelectromechanical or	US-PGPUB;		
		microstructure\$1) and (etch\$3 and	EPO; JPO;		
		((protect\$3 or etch-resist\$3 or etch-stop)	DERWENT;		
1_	16	adj layer)).clm.	IBM_TDB		-
	10		USPAT;	2004/10/12 11:47	'
İ	1	microelectromechanical or	US-PGPUB;		
		microstructure\$1) and (etch\$3 and	EPO; JPO;		-
		(back-side or backside or (back adj side)) and ((protect\$3 or etch-resist\$3 or	DERWENT;		
		etch-stop) adj layer)).clm.	IBM_TDB		
-	12	(MEMS or micromechanical or	HCDAM	0004/10/10	
		microelectromechanical or	USPAT;	2004/10/12 11:48	
ĺ		microstructure\$1) and (etch\$3 and	US-PGPUB;		-
		(back-side or backside or (back adj side))	EPO; JPO; DERWENT;		
		and ((aluminum or polysilicon) adi	IBM TDB		
		layer)).clm.	1207-100		
-	43	(MEMS or micromechanical or	USPAT;	2004/10/12 11:57	
		microelectromechanical or	US-PGPUB;	-501,10,12 11:57	
]	microstructure\$1) and (etch\$3 and (release	EPO; JPO;		
1		adj (mask or layer))).clm.	DERWENT;		
_		/w.1	IBM_TDB		
1 -	21	(release adj mask).clm.	USPAT;	2004/10/12 11:58	
			US-PGPUB;		
			EPO; JPO;		
			DERWENT;		
_	108	(protect\$3 or preveent\$3) and (etch\$3 and	IBM_TDB		1
	100	mask\$3 and backside).clm.	USPAT;	2004/10/12 12:00	
			US-PGPUB;		
			EPO; JPO;		
	1		DERWENT;		1
_	91	(MEMS microstructure\$1) and ((pattern\$3 or	IBM_TDB USPAT;	2004/10/10 11 ==	
	[]	etch\$3 or remov\$3 or form\$3) with	US-PGPUB;	2004/10/12 14:38	
		(backside or back-side)).clm.	EPO; JPO;		
	[.,,	DERWENT;		-
			IBM TDB		1